

mSATA mini

3ME3 Series

Customer: _____

Customer

Part

Number: _____

Innodisk

Part

Number: _____

Innodisk

Model Name: _____

Date: _____

Innodisk Approver	Customer Approver

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REVISION HISTORY

Revision	Description	Date
Preliminary	First Released	May, 2015
1.0	Add random performance info	July, 2015
1.1	Update mechanical drawing	Aug, 2015
1.2	Add 15nm performance, CE , FCC certification	Dec, 2015
1.3	Update 2CH performance	April, 2016

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1. Product Overview

1.1 Introduction of Innodisk mSATA mini 3ME3

Innodisk mSATA mini 3ME3 is designed with mSATA mini form factor by MO-300/MO-300B which established by JEDEC, and support SATA III standard (6.0Gb/s) with excellent performance. Regarding of mechanical interference, Innodisk mSATA mini 3ME3 absolutely replaces the traditional hard disk and makes personal computer, in any field, smaller and easier.

Innodisk mSATA mini 3ME3 effectively reduces the booting time of operation system and the power consumption is less than hard disk drive (HDD), and complies with ATA protocol, no additional drives are required, and can be configured as a boot device or data storage device

1.2 Product View and Models

Innodisk mSATA mini 3ME3 is available in follow capacities within MLC flash ICs.

[mSATA mini 3ME3 8GB](#)

[mSATA mini 3ME3 16GB](#)

[mSATA mini 3ME3 32GB](#)

[mSATA mini 3ME3 64GB](#)

[mSATA mini 3ME3 128GB](#)



Figure 1: Innodisk mSATA mini 3ME3

1.3 SATA Interface

Innodisk mSATA mini 3ME3 supports SATA III(6.0Gb/s) interface, and compliant with SATA I (1.5Gb/s) and SATA II(3.0Gb/s).

2. Product Specifications

2.1 Capacity and Device Parameters

mSATA mini 3ME3 device parameters are shown in Table 1.

Table 1: Device parameters

Capacity	Cylinders	Heads	Sectors	LBA	user space
8GB	15525	16	63	15649200	7,641
16GB	16383	16	63	31277232	15,272
32GB	16383	16	63	62533296	30,533
64GB	16383	16	63	125045424	61,057
128GB	16383	16	63	242255664	118,289

2.2 Performance

Burst Transfer Rate: 6.0Gbps

Table 2: Performance

Capacity	8GB	16GB		32GB	64GB	128GB
		1CH	2CH			
Sequential Read (max.)	100 MB/sec	100 MB/sec	200 MB/sec	200 MB/sec	220 MB/sec	220 MB/sec
Sequential Write (max.)	20 MB/sec	20 MB/sec	40 MB/sec	40 MB/sec	80 MB/sec	80 MB/sec
4KB Random** Read (QD32)	4,100	3,900	6,200	6,200	7,000	6,900
4KB Random** Write (QD32)	5,900	5,300	8,600	8,600	15,800	14,900

Note: the information is based on CrystalDiskMark 3.01 with file size 1000MB test patent

2.3 Electrical Specifications

2.3.1 Power Requirement

Table 2: Innodisk mSATA mini 3ME3 Power Requirement

Item	Symbol	Rating	Unit
Input voltage	V _{IN}	+3.3 DC +- 5%	V

2.3.2 Power Consumption

Table 3: Power Consumption

Mode	Power Consumption (mA)
Read	197 (max.)
Write	241 (max.)
Idle	155 (max.)

* Target: 64GB mSATA mini 3ME3

2.4 Environmental Specifications

2.4.1 Temperature Ranges

Table 4: Temperature range for mSATA mini 3ME3

Temperature	Range
Operating	Standard Grade: 0°C to +70°C
	Industrial Grade: -40°C to +85°C
Storage	-55°C to +95°C

2.4.2 Humidity

Relative Humidity: 10-95%, non-condensing

2.4.3 Shock and Vibration

Table 5: Shock/Vibration Testing for mSATA mini 3ME3

Reliability	Test Conditions	Reference Standards
Vibration	7 Hz to 2K Hz, 20G, 3 axes	IEC 68-2-6
Mechanical Shock	Duration: 0.5ms, 1500 G, 3 axes	IEC 68-2-27

2.4.4 Mean Time between Failures (MTBF)

Table 7 summarizes the MTBF prediction results for various mSATA mini 3ME3 configurations. The analysis was performed using a RAM Commander™ failure rate prediction.

- **Failure Rate:** The total number of failures within an item population, divided by the total number of life units expended by that population, during a particular measurement interval under stated condition.
- **Mean Time between Failures (MTBF):** A basic measure of reliability for repairable items: The mean number of life units during which all parts of the item perform within their specified limits, during a particular measurement interval under stated conditions.

Table 6: mSATA mini 3ME3 MTBF

Product	Condition	MTBF (Hours)
Innodisk mSATA mini 3ME3	Telcordia SR-332 GB, 25°C	>3,000,000

2.5 CE and FCC Compatibility

mSATA mini 3ME3 conforms to CE and FCC requirements.

2.6 RoHS Compliance

mSATA mini 3ME3 is fully compliant with RoHS directive.

2.7 Reliability

Parameter	Value	
Read Cycles	Unlimited Read Cycles	
Wear-Leveling Algorithm	Support	
Bad Blocks Management	Support	
Error Correct Code	Support	
TBW* (Total Bytes Written)	Unit:TB	
8GB	2.4	
16GB	4.8	
32GB	9.6	
64GB	19.2	
128GB	38.4	

2.8 Transfer Mode

mSATA mini 3ME3 support following transfer mode:

- Serial ATA III 6.0Gbps
- Serial ATA II 3.0Gbps
- Serial ATA I 1.5Gbps

2.9 Pin Assignment

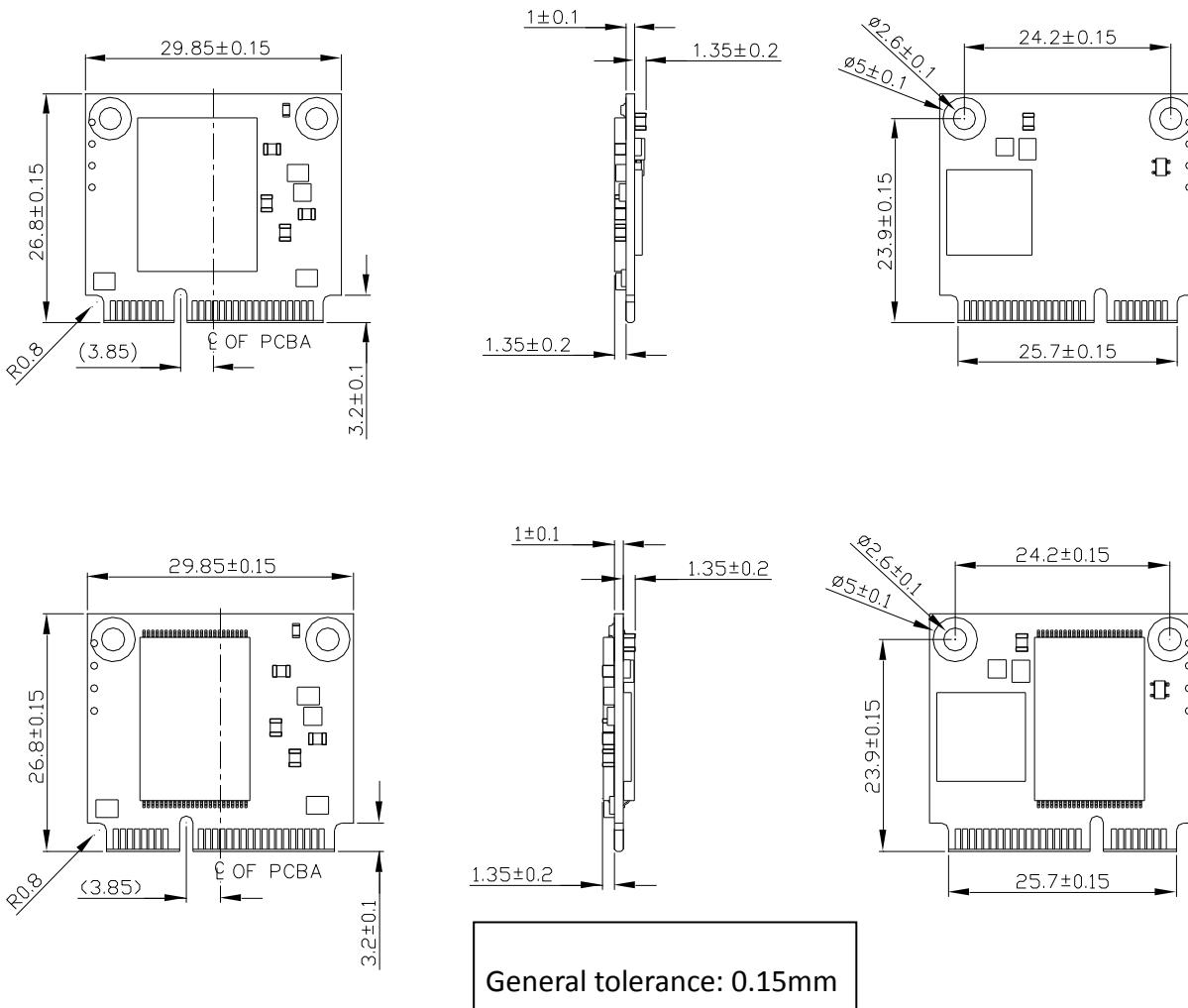
Innodisk mSATA mini 3ME3 uses a standard SATA pin-out. See Table 8 for mSATA mini 3ME3 pin assignment.

Table 7: Innodisk mSATA mini 3ME3 Pin Assignment

Signal Name	Pin #	Pin #	Signal Name
GND	51	52	+3.3V
DAS	49	50	GND
NC	47	48	NC
NC	45	46	NC

NC	43	44	NC
+3.3V	41	42	NC
+3.3V	39	40	GND
GND	37	38	NC
GND	35	36	NC
RX+	33	34	GND
RX-	31	32	NC
GND	29	30	NC
GND	27	28	NC
TX-	25	26	GND
TX+	23	24	+3.3V
GND	21	22	NC
NC	19	20	NC
NC	17	18	GND
GND	15	16	NC
NC	13	14	NC
NC	11	12	NC
GND	9	10	NC
NC	7	8	NC
NC	5	6	NC
NC	3	4	GND
NC	1	2	+3.3V

2.10 Mechanical Dimensions



2.11 Assembly Weight

An Innodisk mSATA mini 3ME3 within flash ICs, 32GB's weight is 8 grams approximately.

2.12 Seek Time

Innodisk mSATA mini 3ME3 is not a magnetic rotating design. There is no seek or rotational latency required.

2.13 NAND Flash Memory

Innodisk mSATA mini 3ME3 uses Multi Level Cell (MLC) NAND flash memory, which is non-volatility, high reliability and high speed memory storage. Each cell stores 2 bits or holds four states per cell. Read or Write data to flash memory for SSD is control by microprocessor.

3. Theory of Operation

3.1 Overview

Figure 2 shows the operation of Innodisk mSATA mini 3ME3 from the system level, including the major hardware blocks.

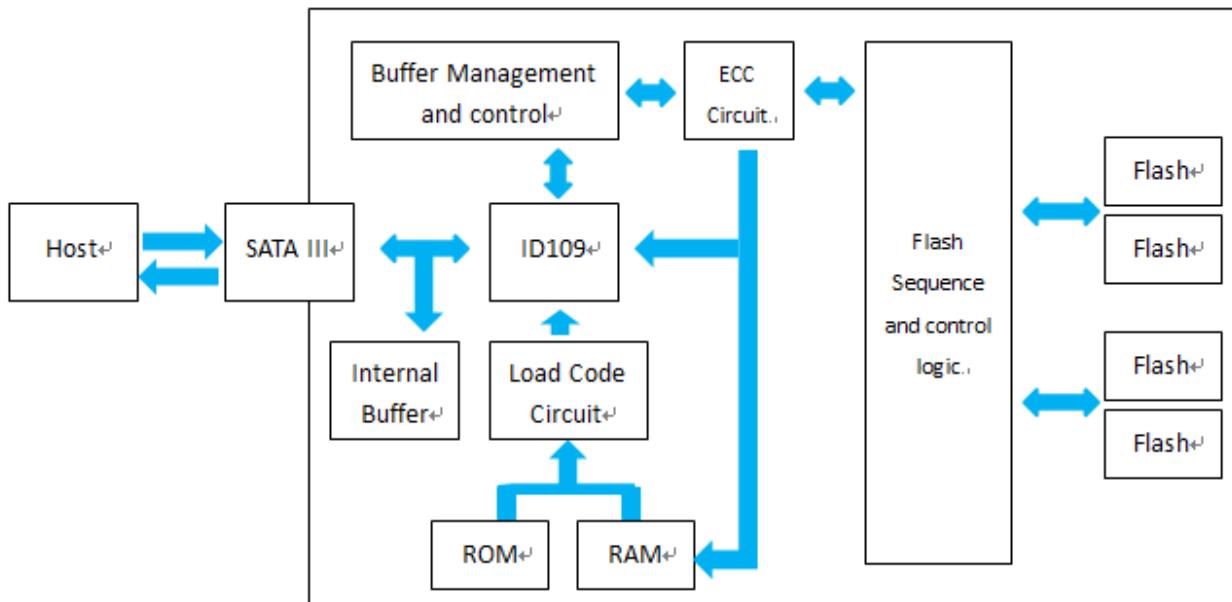


Figure 2: Innodisk mSATA mini 3ME3 Block Diagram

Innodisk mSATA mini 3ME3 integrates a SATA III controller and NAND flash memories. Communication with the host occurs through the host interface, using the standard ATA protocol. Communication with the flash device(s) occurs through the flash interface.

3.2 SATA III Controller

Innodisk mSATA mini 3ME3 is designed with ID 109, a SATA III 6.0Gbps (Gen. 3) controller. The Serial ATA physical, link and transport layers are compliant with Serial ATA Gen 1, Gen 2 and Gen 3 specification (Gen 3 supports 1.5Gbps/3.0Gbps/6.0Gbps data rate). The controller has 2 channels for flash interface.

3.3 Error Detection and Correction

Highly sophisticated Error Correction Code algorithms are implemented. The ECC unit consists of the Parity Unit (parity-byte generation) and the Syndrome Unit (syndrome-byte computation). This unit implements an algorithm that can correct 40 bits per 1024 bytes in an ECC block. Code-byte generation during write operations, as well as error detection during read operation, is implemented on the fly without any speed penalties.

3.4 Wear-Leveling

Flash memory can be erased within a limited number of times. This number is called the **erase cycle limit** or **write endurance limit** and is defined by the flash array vendor. The erase cycle limit applies to each individual erase block in the flash device.

Innodisk mSATA mini 3ME3 uses a static wear-leveling algorithm to ensure that consecutive writes of a specific sector are not written physically to the same page/block in the flash. This spreads flash media usage evenly across all pages, thereby extending flash lifetime.

3.5 Bad Blocks Management

Bad Blocks are blocks that contain one or more invalid bits whose reliability are not guaranteed. The Bad Blocks may be presented while the SSD is shipped, or may develop during the life time of the SSD. When the Bad Blocks is detected, it will be flagged, and not be used anymore. The SSD implement Bad Blocks management, Bad Blocks replacement, Error Correct Code to avoid data error occurred. The functions will be enabled automatically to transfer data from Bad Blocks to spare blocks, and correct error bit.

3.6 Power Cycling

Innodisk's power cycling management is a comprehensive data protection mechanism that functions before and after a sudden power outage to SSD. Low-power detection terminates data writing before an abnormal power-off, while table-remapping after power-on deletes corrupt data and maintains data integrity. Innodisk's power cycling provides effective power cycling management, preventing data stored in flash from degrading with use.

3.7 Garbage Collection

Garbage collection is used to maintain data consistency and perform continual data cleansing on SSDs. It runs as a background process, freeing up valuable controller resources while sorting good data into available blocks, and deleting bad blocks. It also significantly reduces write operations to the drive, thereby increasing the SSD's speed and lifespan.

4. Installation Requirements

4.1 mSATA mini 3ME3 Pin Directions

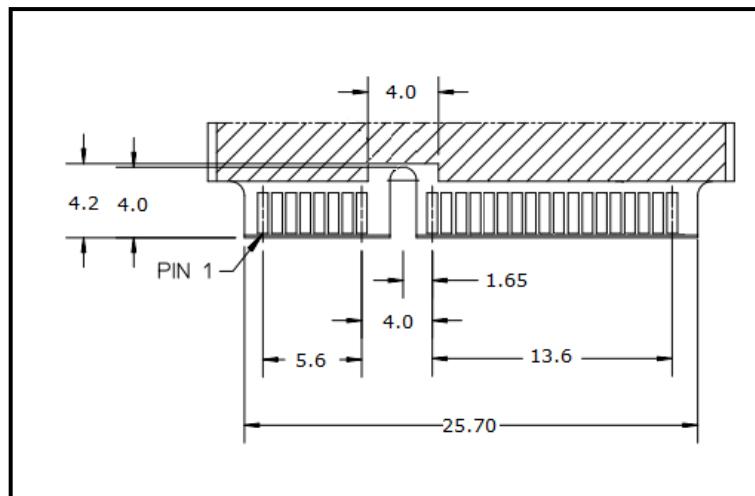


Figure 3: Signal Segment and Power Segment

4.2 Electrical Connections for mSATA mini 3ME3

A Serial ATA device may be either directly connected to a host or connected to a host through an adaptor card. The SATA interface has a separate connector for the power supply. Please refer to the pin description for further details.

4.3 Device Drive

No additional device drives are required. The Innodisk mSATA mini 3ME3 can be configured as a boot device.

5. Part Number Rule

CODE	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21
	D	E	M	S	M	-	6	4	G	D	0	9	B	C	1	D	C	-	X	X	X

Definition

Code 1st (Disk)	Code 13th (Flash mode)
D : Disk	B: Toshiba 15nm
Code 2nd (Feature set)	Code 14th (Operation Temperature)
E : Embedded series	C: Standard Grade (0°C ~ +70°C)
Code 3rd ~5th (Form factor)	W: Industrial Grade (-40°C ~ +85°C)
MSM: mSATA mini	Code 15th (Internal control)
Code 7th ~9th (Capacity)	1~9: TSOP PCB version.
08G:8GB	A~Z: BGA PCB version.
16G:16GB	Code 16th (Channel of data transfer)
32G:32GB	S: Single Channel
64G:64GB	D: Dual Channels
A28:128GB	Code 17th (Flash Type)
	C: Toshiba MLC
Code 10th ~12th (Controller)	Code 19th~21st (Customize code)
D09: ID109	

innodisk

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Innodisk Corporation

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RoHS 自我宣告書(RoHS Declaration of Conformity)

Manufacturer Product: All Innodisk EM Flash and Dram products

一、 宜鼎國際股份有限公司（以下稱本公司）特此保證售予貴公司之所有產品，皆符合歐盟 2011/65/EU 關於 RoHS 之規範要求。

Innodisk Corporation declares that all products sold to the company, are complied with European Union RoHS Directive (2011/65/EU) requirement.

二、 本公司同意因本保證書或與本保證書相關事宜有所爭議時，雙方宜友好協商，達成協議。

Innodisk Corporation agrees that both parties shall settle any dispute arising from or in connection with this Declaration of Conformity by friendly negotiations.

Name of hazardous substance	Limited of RoHS ppm (mg/kg)
Cd	< 100 ppm
Pb	< 1000 ppm
Hg	< 1000 ppm
Chromium VI (Cr+6)	< 1000 ppm
Polybrominated diphenyl ether (PBDE)	< 1000 ppm
Polybrominated Biphenyls (PBB)	< 1000 ppm

立 保 證 人 (Guarantor)

Company name 公司名稱：Innodisk Corporation 宜鼎國際股份有限公司

Company Representative 公司代表人：Richard Lee 李鍾亮

Company Representative Title 公司代表人職稱：CEO 執行長

Date 日期：2014 / 07 / 29



Tel:(02)7703-3000 Fax:(02) 7703-3555 Internet: <http://www.innodisk.com/>

REACH Declaration of Conformity

Manufacturer Product: All Innodisk EM Flash and Dram products

1. 宜鼎國際股份有限公司（以下稱本公司）特此保證此售予貴公司之產品，皆符合歐盟化學品法案(Registration , Evaluation and Authorization of Chemicals : REACH)之規定(<http://www.echa.europa.eu/de/candidate-list-table> last updated: 16/05/2014)。所提供之產品包含：(1) 產品或產品所使用到的所有原物料；(2)包裝材料；(3)設計、生產及重工過程中所使用到的所有原物料。

We Innodisk Corporation hereby declare that our products are in compliance with the requirements according to the REACH Regulation (<http://www.echa.europa.eu/de/candidate-list-table> last updated: 16/06/2014).

Products include : 1) Product and raw material used by the product ; 2) Packaging material ; 3) Raw material used in the process of design, production and rework

2. 本公司同意因本保證書或與本保證書相關事宜有所爭議時，雙方宜友好協商，達成協議。

InnoDisk Corporation agrees that both parties shall settle any dispute arising from or in connection with this Declaration of Conformity by friendly negotiations.

立 保 證 書 人 (Guarantor)

Company name 公司名稱：InnoDisk Corporation 宜鼎國際股份有限公司

Company Representative 公司代表人：Richard Lee 李鍾亮

Company Representative Title 公司代表人職稱：CEO 執行長

Date 日期：2014 / 07 / 29



Certificate

Issue Date: July 29, 2015
 Ref. Report No. ISL-15LE319CE

Product Name : mSATA mini
 Model(s) : mSATA mini 3\$*#-&
 (\$:Flash type: (S:SLC,I:iSLC,M:MLC);
 *:Product line: (E:Embedded, G:EverGreen, R:InnoRobust);
 #:Controller: (empty:106/107/167/170, 2:201/ 202, 3:108/109);
 &:Product feature: (P:with DRAM, empty:without DRAM))
 Responsible Party : Innodisk Corporation
 Address : 5F.No.237, Sec. 1, Datong Rd., Xizhi Dist., New Taipei City 221,
 Taiwan (R.O.C.)

We, International Standards Laboratory, hereby certify that:

The device bearing the trade name and model specified above has been shown to comply with the applicable technical standards as indicated in the measurement report and was tested in accordance with the measurement procedures specified in European Council Directive- EMC Directive 2004/108/EC.
 The device was passed the test performed according to :



Standards:

EN 55022: 2010+AC2011 and CISPR 22: 2008 (modified)
 EN 61000-3-2: 2006+A1:2009 +A2:2009 and IEC 61000-3-2: 2005+A1:2008 +A2:2009
 EN 61000-3-3: 2013 and IEC 61000-3-3: 2013
 EN 55024: 2010 and CISPR 24: 2010
 EN 61000-4-2: 2009 and IEC 61000-4-2: 2008
 EN 61000-4-3: 2006+A1: 2008 +A2: 2010 and
 IEC 61000-4-3:2006+A1: 2007+A2: 2010
 EN 61000-4-4:2012 and IEC 61000-4-4:2012

I attest to the accuracy of data and all measurements reported herein were performed by me or were made under my supervision and are correct to the best of my knowledge and belief. I assume full responsibility for the completeness of these measurements and vouch for the qualifications of all persons taking them.

International Standards Laboratory

Jim Chu / Director

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Lung-Tan LAB:

No. 120, Lane 180, Hsin Ho Rd., Lung-Tan Dist.,
 Tao Yuan City 325, Taiwan
 Tel: 886-3-407-1718; Fax: 886-3-407-1738



Certificate

Issue Date: July 29, 2015
 Ref. Report No. ISL-15LE319FB

Product Name : mSATA mini
 Model(s) : mSATA mini 3\$*#-&
 (\$:Flash type: (S:SLC,I:iSLC,M:MLC);
 *:Product line: (E:Embedded, G:EverGreen, R:InnoRobust);
 #:Controller: (empty:106/107/167/170, 2:201/ 202, 3:108/109);
 &:Product feature: (P:with DRAM, empty:without DRAM))
 Applicant : Innodisk Corporation
 Address : 5F No.237, Sec. 1, Datong Rd., Xizhi Dist., New Taipei City 221,
 Taiwan (R.O.C.)

We, International Standards Laboratory, hereby certify that:

The device bearing the trade name and model specified above has been shown to comply with the applicable technical standards as indicated in the measurement report and was tested in accordance with the measurement procedures specified. (refer to Test Report if any modifications were made for compliance).



Standards:

FCC CFR Title 47 Part 15 Subpart B: 2014- Section 15.107 and 15.109

ANSI C63.4-2009

Industry Canada Interference-Causing Equipment Standard ICES-003 Issue 5: 2012

Class B

I attest to the accuracy of data and all measurements reported herein were performed by me or were made under my supervision and are correct to the best of my knowledge and belief. I assume full responsibility for the completeness of these measurements and vouch for the qualifications of all persons taking them.

International Standards Laboratory

Jim Chu / Director

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